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## **Innovative Silicon's Serguei Okhonin Receives Prestigious "Young Alumni" Award**

*Chief scientist recognized for next-generation memory technology developments*

SANTA CLARA, Calif. — August 13, 2009 — Innovative Silicon, Inc. (ISI), developer of the Z-RAM® zero-capacitor floating body memory (FB) technology, today announced that Dr. Serguei Okhonin, the company's co-founder and chief scientist, won the 2009 [Young Alumni Award](#) from the Alumni Association of [Ecole Polytechnique Fédérale de Lausanne](#) (A3-EPFL). Young Alumni Awards were given only to inventors of solutions developed primarily outside the domain of the EPFL or other academic institutions.

Dr. Okhonin and two runners-up were recognized during the organization's flagship event. As the top prize winner, Dr. Okhonin was recognized for his role in advancing semiconductor memory technology for future generations. Dr. Okhonin is a co-founder of ISI and is the primary inventor of the original Z-RAM memory technology. He has continued to drive ongoing enhancements to make Z-RAM the lowest-cost and most-scalable, random-access memory technology in the world.

### **About Dr. Serguei Okhonin**

Dr. Okhonin received his M. Sc. in Physics from Novosibirsk State University in 1980, and his PhD degree from Ecole Polytechnique Fédérale de Lausanne (EPFL) in 2001. From 1980 to 1993, he worked as research associate at the Institute of Semiconductor Physics, Novosibirsk, Russia, focusing on semiconductor device physics. From 1994 to 2003, he worked as research associate at l'Institut de Micro et Optoélectronique (IMO) and Laboratoire d'Electronique Générale (LEG) at Ecole Polytechnique Fédérale de Lausanne (EPFL). He took part in several European projects focused on advanced CMOS technology development. In 2002, he co-founded Innovative Silicon, developing a new floating-body single transistor memory technology. He has authored or coauthored more than 50 papers and filed more than 40 patents. In 2007, Dr. Okhonin was named *EE Times* ACE Awards "Innovator of the Year" Finalist for his invention of the second generation of Z-RAM. Dr. Okhonin has also served in the program committees of the [ASDAM](#) and [ESSDERC](#) international conferences.

### **About Innovative Silicon**

Innovative Silicon, Inc. (ISI) licenses its Z-RAM® ultra-dense memory technology to stand-alone DRAM manufacturers so they may manufacture the lowest-cost, most-advanced memory ICs. Licensees include Hynix Semiconductor for use in advanced DRAM chips. The heart of the Z-RAM technology is the “zero-capacitor,” single-transistor floating-body bit-cell that eliminates the complex capacitor found in today’s DRAM technologies – making Z-RAM the world’s lowest-cost and most-scalable memory technology. Since 2003, the company has closed \$47 million in venture capital funding, received numerous industry awards such as *IEEE Spectrum Magazine*’s “2007 Emerging Technology Most Likely to Succeed,” been granted dozens of patents, and established global R&D, engineering and support centers in Europe, Asia and North America. For more information see [www.z-ram.com](http://www.z-ram.com).

Z-RAM is a registered trademark of Innovative Silicon, Inc. or its subsidiaries in the United States and other countries.

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